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ABSTRACT OF THE DISCLOSURE

A method comprising introducing an interconnect structure in an opening through a dielectric over a contact point, and introducing a conductive shunt material through a chemically-induced oxidation-reduction reaction. A method comprising introducing an interconnect structure in an opening through a dielectric over a contact point, introducing a conductive shunt material having an oxidation number over an exposed surface of the interconnect structure, and reducing the oxidation number of the shunt. An apparatus comprising a substrate comprising a device having contact point, a dielectric layer overlying the device with an opening to the contact point, and an interconnect structure disposed in the opening comprising an interconnect material and a different conductive shunt material.